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EXAMINER

MALSAWMA, LALRINFAMKIM HMAR

ART UNIT

PAPER NUMBER

2825

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Please find below and/or attached an Office communication concerning this application or proceeding.

**Office Action Summary**

Application N .

09/191,930

Applicant(s)

CHIANG ET AL.

Examiner

Lex Malsawma

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

**Period for Reply**

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

**Status**

- 1) ☒ Responsive to communication(s) filed on 06 February 2002.
- 2a) ☒ This action is **FINAL**. 2b) ☐ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

**Disposition of Claims**

- 4) ☒ Claim(s) 17 and 20-44 is/are pending in the application.
- 4a) Of the above claim(s) \_\_\_\_\_ is/are withdrawn from consideration.
- 5) ☐ Claim(s) \_\_\_\_\_ is/are allowed.
- 6) ☒ Claim(s) 17 and 20-44 is/are rejected.
- 7) ☐ Claim(s) \_\_\_\_\_ is/are objected to.
- 8) ☐ Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

**Application Papers**

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on \_\_\_\_\_ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
- Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- 11) ☐ The proposed drawing correction filed on \_\_\_\_\_ is: a) ☐ approved b) ☐ disapproved by the Examiner.
- If approved, corrected drawings are required in reply to this Office action.
- 12) ☐ The oath or declaration is objected to by the Examiner.

**Priority under 35 U.S.C. §§ 119 and 120**

- 13) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some \* c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- \* See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).
- a) ☐ The translation of the foreign language provisional application has been received.
- 15) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

**Attachment(s)**

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☒ Information Disclosure Statement(s) (PTO-1449) Paper No(s) 11
- 4) ☐ Interview Summary (PTO-413) Paper No(s). \_\_\_\_\_
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other:

## DETAILED ACTION

### *Claim Rejections - 35 USC § 103*

1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

2. Claims 17, 24-30, and 35-37 are rejected under 35 U.S.C. 103(a) as being unpatentable over Usami (6,222,269) in view of Havemann (5,751,066) and Doo (4,153,988).

#### *Regarding Claim 17:*

Usami discloses (in Figs. 2A-3C and cols. 5-7) a method of forming an interconnect structure, comprising:

- forming a first layer 4 of a first dielectric material on a substrate;
- patterning the first layer (Fig. 2B);
- depositing conductive material 13 over the patterned first layer;
- planarizing the conductive material such that a plurality of interconnect lines 3 are formed including a first and a second "wide" interconnect lines (i.e., note the two interconnect lines "3" on the right side in Fig. 2D) and a third and fourth "thin" interconnect lines (e.g., the third line being the "thin" interconnect line "3" in the center and the fourth being the left most interconnect line "3" in Fig. 2D);
- forming a mask layer 14 over the interconnect lines 3 and patterned first layer 4 (Fig. 3A);

patterning the mask layer 14 such that the first and second “wide” interconnect lines and a first portion of the patterned first layer 4 are covered, and the third and fourth “thin” interconnect lines and a second portion of the patterned first layer 4 are uncovered (note in Fig. 3A, about half of the left most interconnect line “3”, i.e., the fourth “thin” interconnect line, is uncovered such that it could be said that the fourth “thin” interconnect line is uncovered);

removing the dielectric material 4 from the uncovered portion (Fig. 3B);

removing the second portion of the patterned first layer 4 (Fig. 3B); and

depositing a second layer 5 of a second dielectric material between the third and fourth “thin” interconnect lines, the second dielectric material having a smaller dielectric constant than the first dielectric material (Fig. 3C and col. 6, lines 3-9).

Usami **lacks** specifying the plurality of interconnect lines includes power interconnect lines (first and second) and signal interconnect lines (third and fourth), however, it is important to note that Usami does not specify whether the interconnect lines “3” may or may not include a combination of power lines and signal lines. Note Usami specifies that a low-dielectric-constant material between signal lines reduces parasitic capacitance and crosstalk (see Usami, col. 8, lines 14-20). Havemann **teaches** a method of forming two different dielectric materials between a plurality of interconnect lines located on the same level of metallization, wherein the method comprises: forming a low-dielectric-constant material 34 (note Fig. 3B) between closely-spaced interconnect lines 18 in order to reduce unwanted capacitance between lines 18 (note col. 2, lines 35-37); and forming a “higher” dielectric-constant material 26 between interconnect lines 16 where capacitance is not as critical (note abstract, line 3-5). Doo is **cited only** to show it was very well known in the art that problems associated with power lines (i.e., “driver noise”, note

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col. 3, lines 51-55) can be reduced by increasing the capacitance of the power line (note col. 4, lines 13-16). The formula for capacitance is well known to any one in the art, and one of ordinary skill in the art would have known that, for a given separation between a pair of formed interconnect lines, the capacitance between the pair can be readily increased or decreased by forming a high-k or low-k dielectric (respectively) in between the pair of interconnect lines. In view of Havemann and Doo, it would have been obvious to one of ordinary skill in the art to modify Usami by utilizing the interconnect lines "3" for a combination of power lines and signal lines on the same level of metallization because the two dielectric materials ("4" and "5") can be readily utilized to increase capacitance between power lines and to decrease parasitic capacitance between signal lines.

*Regarding Claims 24 and 35:*

Usami discloses a method of forming an interconnect structure, comprising:

forming, on a substrate, a first plurality of interconnect lines 3 and a first intralayer dielectric 4 disposed between the first plurality of interconnect lines (Fig. 2D);

removing a portion of the first intralayer dielectric 4 (Fig. 3B); and

forming a second intralayer dielectric 5 on the substrate where the first intralayer dielectric was removed (Fig. 3C).

Usami **lacks** the following: (1) forming a second plurality of interconnect lines in the second interlayer dielectric, and (2) specifying whether the interconnect lines 3 may or may not include signal lines and power lines. In regards to lacked limitation (1), it is noted Usami discloses forming all conductive lines simultaneously, wherein a plurality of interconnect lines will exist within the second interlayer dielectric layer when said second interlayer dielectric layer

is formed. Havemann **teaches** (in Figs. 2A-3B) a method of forming two different dielectric materials between interconnect layer on the same level of metallization, wherein the method can include forming a first plurality of interconnect lines 16 with a first dielectric material between the lines 16, and then forming a second plurality of interconnect lines 18 with a second dielectric material between the lines 18. It is important to note Haveman also teaches (in Figs. 5A-6E) the interconnect lines 16 and 18 may be formed simultaneously instead of forming two pluralities that would require at least two masking/patterning steps, in other words, in view of Havemann, one of ordinary skill in the art would have realized that the interconnect lines of Usami could also be formed in two pluralities, wherein forming two pluralities would require the utilization of at least two masking/patterning steps. In regards to lacked limitation (2), Doo is **cited only** to show that one of ordinary skill in the art would have realized that the interconnect lines of Usami (or Havemann) are ideal for power lines and signal lines. Doo discloses the well-known problems associated with signal lines and power lines (note col. 3, lines 28-55), wherein problems such as signal propagation delay can be reduced by utilizing a low-dielectric-constant material and problems associated with power lines can be reduced by increasing capacitance of the power lines (note col. 4, lines 13-16), in other words, it was well known in the art to utilize a low-dielectric-constant material between signal lines and to increase the capacitance of power lines in order to effectively decouple noise from the power lines, wherein utilizing a “higher” dielectric-constant material between the power lines is a relatively quick and easy way to increase the capacitance between the power lines. It would have been an obvious matter of design choice for one of ordinary skill in the art to modify Usami by (i) forming two pluralities of interconnect lines instead of simultaneously forming all interconnect lines and (ii) specifying

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that the interconnect lines comprise signal lines and power lines because of the following reasons: (1) Havemann teaches that either a simultaneous process or two separate patterning processes may be utilized to form interconnect lines on the same level of metallization, and one of ordinary skill in the art would have realized that Usami can also be modified by forming the interconnect lines utilizing two separate patterning processes, wherein one would have realized that two separate patterning processes will increase process time and complexity without any apparent significant benefits, however, one could obviously choose to do so; and (2) the methods disclosed by Usami and Havemann are ideal for acquiring a combination of signal lines and power lines on the same level of metallization, since it was well known in the art (as shown by Doo) that it is desirable to form a low-dielectric-constant material between adjacent signal lines and that it is desirable to increase the capacitance of power lines (e.g., by incorporating a “higher” dielectric-constant material between adjacent power lines). *Specifically regarding Claim 35:* Usami (in view of Havemann and Doo) would obviously result in the second intralayer dielectric having a larger dielectric constant than that of the first intralayer dielectric because the second intralayer dielectric layer would be formed between the power lines wherein signal propagation delay is not critical (i.e., power lines in integrated circuits generally distribute direct current, with the exception of noise/ripple on the DC power lines). In any case, Doo shows that capacitance of power lines should be increased so that noise can be effectively decoupled from the power lines, i.e., a “higher” dielectric-constant material will increase the capacitance between the power lines.

*Regarding Claim 25:*

Usami (in view of Havemann and Doo) discloses a dielectric constant of the first intralayer dielectric is different from a dielectric constant of the second intralayer dielectric.

*Regarding Claim 26:*

In general, the instant claim contains limitations for forming interconnect lines by a damascene process, and although Usami lacks forming a second plurality of interconnect lines, Havemann teaches that interconnect lines on the same level of metallization can be formed by utilizing a simultaneous process or plural processes. The instant claim is held obvious over the cited references because of the following reasons: (a) Usami discloses a damascene process, in Figs. 2A-2D, wherein the plurality of conductive lines 3 are formed by etching trenches in the first intralayer dielectric 4, depositing a conductive material 13, and polishing the conductive material such that the conductive material is substantially removed except for that which is in the trenches; (b) Usami disclose forming all conductive lines simultaneously using a single damascene process instead of, for example, forming the conductive lines utilizing two separate damascene processes; (c) one of ordinary skill in the art would have readily recognized that Usami could be modified, if so desired, by forming several “pluralities” of conductive lines utilizing two or more damascene processes, especially since Havemann teaches interconnect lines on the same level of metallization, having two different dielectrics therebetween, can be formed utilizing a simultaneous process or plural processes; (d) forming the conductive lines in several “pluralities” would increase process time and complexity without significant benefits, however, one could obviously choose to do so if time and cost are not an issue; therefore, if one chooses to form the conductive lines (of Usami) in several “pluralities” (i.e., in a first and second



plurality of lines), then it would have been obvious to utilize the process steps in “(a)” when forming each of the several “pluralities” of conductive lines.

*Regarding Claim 27:*

Usami discloses a method of forming an interconnect structure comprising:

- (A) forming a first dielectric layer 4 on a substrate;
- (B) forming a plurality of interconnect lines 3 in the first dielectric layer 4 (Fig. 2D);
- (C) removing a portion of the first dielectric layer 4 (Fig. 3B); and

(D) forming a second dielectric layer 5 on the substrate where the portion of the first dielectric layer was removed, wherein the plurality of interconnect lines 3 are positioned in the first and second dielectric layers.

Usami **lacks** performing step “(B)” after step “(D)” and specifying that the interconnection lines 3 comprise a plurality signal lines and a power line. In view of Havemann and Doo, it would have been an obvious matter of design choice to specify that interconnect lines 3 comprise a combination of signal lines and a power line, since Usami’s disclosure is ideal for such a specification (see above, Regarding Claims 17 and 24, for detailed reasoning for such a specification/utilization of the interconnect lines 3). Only the lacked limitation of performing step “(B)” after step “(D)” will be currently addressed in detail, in other words, in reference to the instant claim, Usami **lacks** forming a plurality of interconnect lines simultaneously in the first and second dielectric layers. In general, Usami discloses the inventive aspect of Applicants’ disclosure, i.e., Usami discloses forming an interconnect structure comprising two different dielectric layers, having different dielectric constants, formed between a plurality of interconnect lines such that the dielectric layers and the interconnect lines are on the same level of

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metallization, wherein incorporating the two dielectric layers can at least prevent crosstalk (and reduce parasitic capacitance) between signal lines having the “lower” dielectric constant of the two dielectric layers. Although the instant claim recites a different sequence than that disclosed by Usami, the instant claim is held obvious because of the following reasons: Usami discloses the general conditions of the instant claim; the instant claimed process sequence may require more processing steps than Usami's disclosed sequence, i.e., the first dielectric will need to be etched twice in both sequences, however, in the instant claimed sequence, it may not be possible to simultaneously etch openings in both dielectric layers using the same mask or etching chemistry, since the dielectric layers would be formed of different materials; given Usami's disclosure, one of ordinary skill in the art would have readily recognized that forming all the interconnecting lines after forming the second dielectric layer would be a matter of design choice, since such a choice would not reduce the number of process steps; therefore, it would have been an obvious matter of design choice for one of ordinary skill in the art to modify Usami by performing step “(B)” after step “(D)”, since there seems to be no significant benefit for choosing such a modification.

*Regarding Claim 28:*

Usami discloses the dielectric constant of the first dielectric is different than that of the second dielectric.

*Regarding Claim 29:*

The instant claim, similar to Claim 26, contains limitations for forming the interconnect lines using a damascene process. With similar reasoning applied to claim 26 above, the instant

claim is held obvious over the cited references, i.e., a damascene process as instantly claim was well known and used in the art.

*Regarding Claims 30, 36, and 37:*

In general, Usami's disclosure is applicable to semiconductor device manufacturing (note col. 1, lines 5-9), therefore, it would have been obvious to one of ordinary skill in the art to acquire an integrated circuit device comprising a substrate having an interconnect structure thereon by the method disclosed by Usami (in view Havemann and Doo).

3. Claims 20-23, 31-34, and 38-44 are rejected under 35 U.S.C. 103(a) as being unpatentable over Havemann (5,751,066) in view of Doo (4,153,988).

*Regarding Claims 20, 21, 31, 38, 39, 42, and 43:*

Havemann discloses a method of forming an interconnect structure, comprising:

forming a first layer of a conductive material (15, 17) on a substrate 12 (Fig. 5A);

forming a first pair of interconnect lines 16 and a second pair of interconnect lines 18 (Fig. 5C);

depositing a first dielectric material 26 over and between the first pair and the second pair (Fig. 5D);

forming a masking layer 50 over the first pair and the second pair and first dielectric material (Fig. 5E and col. 8, lines 26-32);

patterning the mask layer 50 such that one portion of the dielectric material 26 between one pair is covered and another pair is uncovered (Fig. 5E);

removing the portion of the dielectric material that is uncovered (Fig. 6A);

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removing the patterned mask layer (Fig. 6B); and

depositing a second dielectric material 34 having a different dielectric constant than a dielectric constant of the first dielectric material 4 (Fig. 6C and col. 8, lines 36-37), wherein the first dielectric material 26 has a dielectric constant greater than that of the second dielectric material 34.

Havemann **lacks** specifically disclosing that lines "16" are for power distribution and that lines "18" are for carrying signals. Doo is **cited only** to show that one of ordinary skill in the art would have readily recognized that the interconnect lines "16" and "18" (of Havemann) are ideal for power lines and signal lines, respectively. Doo discloses the well-known problems associated with signal lines and power lines (note col. 3, lines 28-55), wherein problems such as signal propagation delay can be reduced by utilizing a low-dielectric-constant material and problems associated with power lines can be reduced by increasing capacitance of the power lines (note col. 4, lines 13-16), in other words, it was well known in the art to utilize a low-dielectric-constant material between signal lines and to increase the capacitance of power lines in order to effectively decouple noise from the power lines, wherein utilizing a "higher" dielectric-constant material between the power lines is a relatively quick and easy way to increase the capacitance between the power lines. It would have been obvious to one of ordinary skill in the art to modify Havemann by specifying that interconnect lines "16" and "18" are utilized to distribute power and carry signals, respectively, because the interconnect structure formed by Havemann is ideal for such a utilization. *Specifically regarding Claim 31:* Choosing to utilize lines "16" as the one pair renders Claim 31 obvious.

*Regarding Claims 22, 32, 40, and 41:*

These claims contain limitations for forming the low-dielectric-constant material between the signal lines before forming the “higher” dielectric-constant material between the power lines. Given Havemann, one of ordinary skill in the art could have modified the process sequence shown in Figs. 5C-6C with relative ease by performing the following modifications: replacing material “26” with material “34” in the process shown in Fig. 5D; forming/patterning the mask “50” to cover lines “18” instead of lines “16”(in the process shown in Fig. 5E); removing material “34” not covered by mask “50”, i.e., removing material “34” over lines “16” (in the process shown in Fig. 6A); removing the mask “50” (in the process shown in Fig. 6B); and forming material “26” over lines “16” wherein the material “26” would overlap material “34” in the process shown in Fig. 6C. Such a modification would not have required extensive experimentation or research because, in general, the modification would be based on design choice, i.e., based on choosing first to form the low-dielectric-constant material “34” and then patterning the mask “50” accordingly, therefore, the instant claims are held as obvious design choice modifications (of Havemann) that would have been relatively easily performed by one of ordinary skill in the art.

*Regarding Claim 23:*

Havemann discloses a method of making in-plane decoupling capacitors, comprising:  
forming a first plurality of conductive lines 16 on an insulating substrate 12, the first plurality of conductive lines having a first dielectric 26 therebetween (Figs. 1A-2B); and

forming a second plurality of conductive lines 18 on the insulating substrate 12, the second plurality of conductive lines having a second dielectric material 34 therebetween (Figs. 2D-3B);

wherein the first dielectric constant is greater than a dielectric constant of the second dielectric.

Havemann **lacks** specifically disclosing that conductive lines "16" are power lines and that conductive lines "18" are signal lines. Doo is **cited only** to show that one of ordinary skill in the art would have readily recognized that the interconnect lines "16" and "18" (of Havemann) are ideal for power lines and signal lines, respectively. With similar reason applied above, the instant claim is held obvious over the cited references (See above, *Regarding Claims 20, 21, 31, 38, 42, and 43*, for detailed reasoning).

*Regarding Claims 33, 34, and 44:*

Havemann's disclosure is applicable to semiconductor device manufacturing, therefore, it would have been obvious to one of ordinary skill in the art to acquire an integrated circuit device comprising a substrate having an interconnect structure thereon by the method disclosed by Havemann (in view of Doo).

***Remarks***

4. Applicants' remarks have been fully considered but they are not persuasive. In general, Applicants amended the claims to include limitations for forming power lines and signal lines, and Applicants submit that the previously cited references do not teach or suggest forming power lines, patterning the power lines and signal lines independently, and depositing a smaller

dielectric constant material between signal lines. New references have been cited in the current Office Action in order to clearly address the amendments to the claimed invention. In general, the new references (e.g., Havemann and Doo) were cited to show that a process comprising forming two dielectrics, each having a different dielectric constants, on the same level of metallization is an ideal process for acquiring a combination of signal lines and power lines. Although Usami and Havemann do not specifically disclose a combination of power lines and signal lines, one of ordinary skill in the art would have readily recognized that their disclosures are ideal for such a combination, and Doo has been cited to show that one of ordinary skill in the art would have realized that the low-constant-dielectric material would be located between signal lines and the “higher” dielectric-constant material would be located between power lines.

### *Conclusion*

5. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

Crafts (5,288,949), Jeng (6,054,769), Parikh (6,225,207 B1), and Ball et al. (6,246,112 B1) are cited to show it was well known in the art to form a combination of signal lines and power lines on the same level of metallization or to show another process for forming two different dielectric constant materials on the same level of metallization.

6. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

7. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Lex Malsawma whose telephone number is 703-306-5986.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Matthew Smith can be reached on 703-308-1323. The fax phone numbers for the organization where this application or proceeding is assigned are 703-872-9318 for regular communications and 703-872-9319 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0956.

Lex Malsawma



May 6, 2002



MATTHEW SMITH  
SUPERVISORY PATENT EXAMINER  
TECHNOLOGY CENTER 2800